

Supporting Information for

Enhanced magnetic anisotropy of iridium dimers on antisite defects of two-dimensional transition-metal dichalcogenides

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S1. Optimized lattice parameters of the pristine and Janus TMD nanosheets

Table S1. Optimized in-plane lattice constant of the pristine MX_2 and Janus MXY TMD nanosheets.

TMDs	a (Å)	TMDs	a (Å)
MoS ₂	3.18	WS ₂	3.18
MoSe ₂	3.32	WSe ₂	3.32
MoTe ₂	3.55	WTe ₂	3.55
MoSSe	3.22	WSSe	3.25
MoSTe	3.32	WSTe	3.37
MoSeTe	3.43	WSeTe	3.43

S2. The formation energies of the antisite defects from TMD monolayers

Before constructing the $\text{Ir}_2@\text{TMD-X}_M$ system, it is necessary to indicate the formation energy of the antisite defect in our study. Here, we calculated the formation energy E_f of antisite defects X_M of TMD monolayers (see Fig. S1), which is expressed as,

$$E_f = E_{\text{defect}} - E_{\text{pure}} + \mu_M - \mu_X \quad (2-1)$$

where E_{defect} and E_{pure} present the total energies of TMD monolayer with and without antisite defects. μ_M and μ_X are the chemical potentials of metal M and chalcogen X atoms from antisite defects, respectively. The chemical potential of M and X in MX_2 should satisfy $\mu_M + 2\mu_X = \mu_M^0 + 2\mu_X^0 + \Delta H_{\text{MX}_2}$, where μ_M^0 and μ_X^0 are the chemical potential of M and X in their bulk form, respectively. ΔH_{MX_2} is the formation enthalpy of the MX_2 monolayer. Note that it is difficult to specify the exact value of the chemical potential, we can only provide ranges as $\mu_M^0 + \Delta H_{\text{MX}_2} \leq \mu_M \leq \mu_M^0$, $\mu_X^0 + \frac{1}{2}\Delta H_{\text{MX}_2} \leq \mu_X \leq \mu_X^0$ based on the M-rich and X-rich conditions. The Janus-MXY TMD (X, Y = S/Se/Te; X \neq Y) monolayer is synthesized by replacing one X atom layer with a Y atom layer from the MX_2 monolayer. Based on this synthesis process, it is logical to assume that the chemical potential range is comparable to that of the MX_2 (MY_2) monolayer.

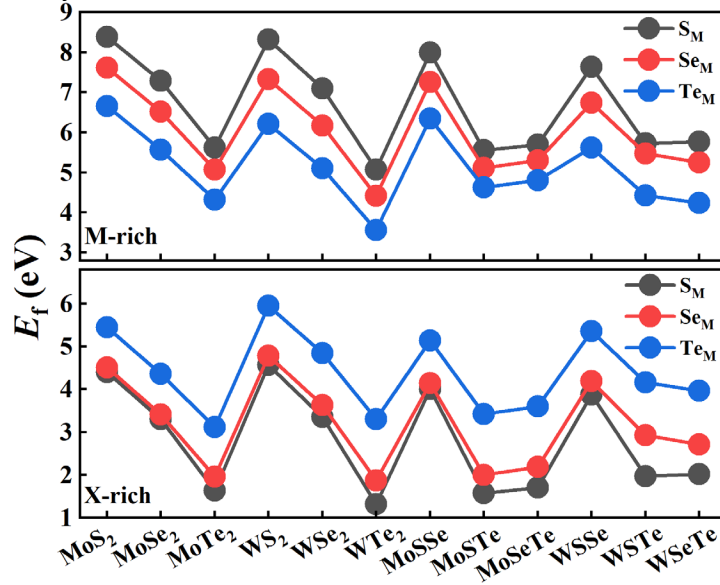


Fig. S1 The formation energies E_f of antisite defects in tradition MX_2 and Janus MXY TMD monolayers.

S3. Stability comparison of Ir₂ adsorbed on different sites of MoS₂-S_{Mo}.

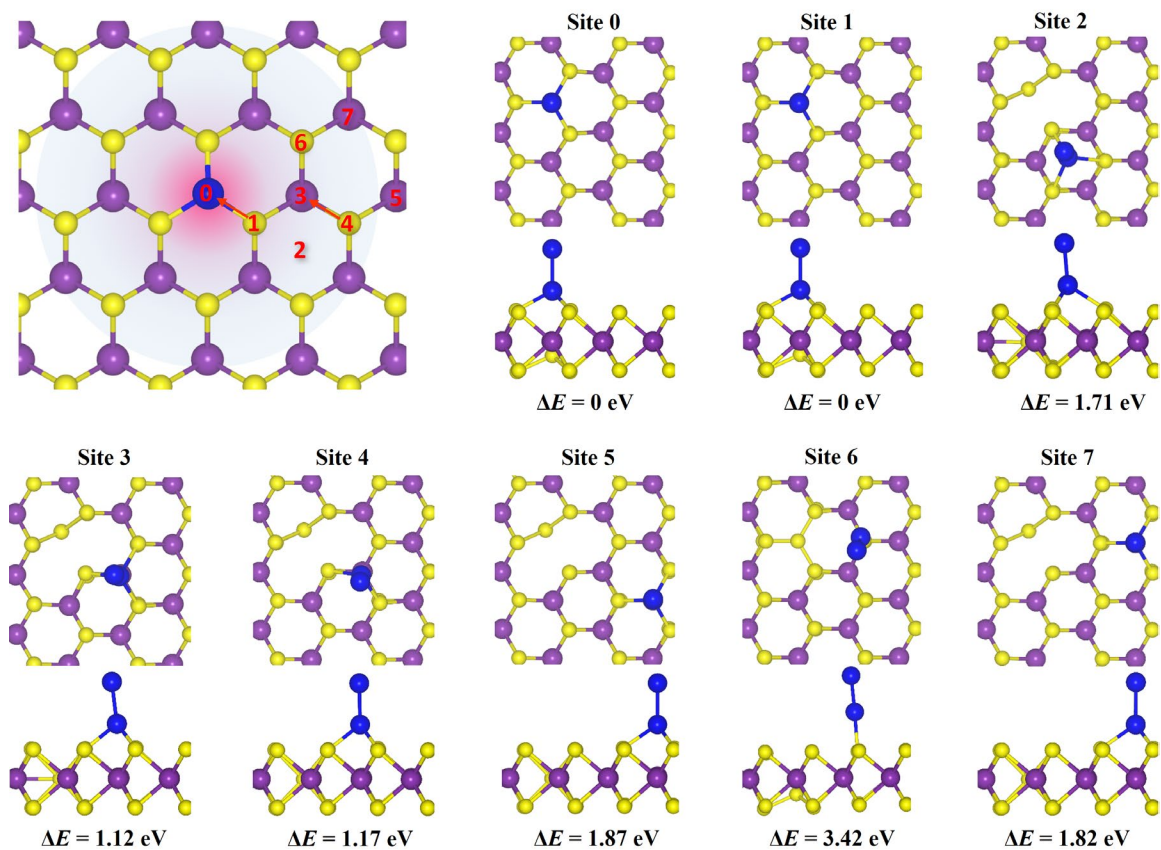


Fig. S2 Top view, side view and energy difference ΔE of Ir₂ adsorbed at the site 0-7 of MoS₂-S_{Mo} at optimal energy. Here, $\Delta E = E_{tot}^n - E_{tot}^0$, where E_{tot}^n and E_{tot}^0 present the total energy of Ir₂@MoS₂-S_{Mo} at the site n (n = 1-7) and site 0, respectively.

S4. The average electrostatic potential difference of Janus TMDs with antisite defects.

Table S2. The average electrostatic potential difference ΔV (eV) of Janus TMDs with antisite defects.

TMDs	S _{Mo}	Se _{Mo}	Te _{Mo}	TMDs	S _W	Se _W	Te _W
MoSSe(↑)	0.560	0.725	0.710	WSSe(↑)	0.809	0.711	0.681
MoSSe(↓)	-0.560	-0.725	-0.710	WSSe(↓)	-0.809	-0.711	-0.681
MoSTe(↑)	1.276	1.276	1.338	WSTe(↑)	1.219	1.416	1.303
MoSTe(↓)	-1.276	-1.276	-1.338	WSTe(↓)	-1.219	-1.416	-1.303
MoSeTe(↑)	0.566	0.563	0.689	WSeTe(↑)	0.785	0.661	0.663
MoSeTe(↓)	-0.566	-0.563	-0.689	WSeTe(↓)	-0.785	-0.661	-0.663

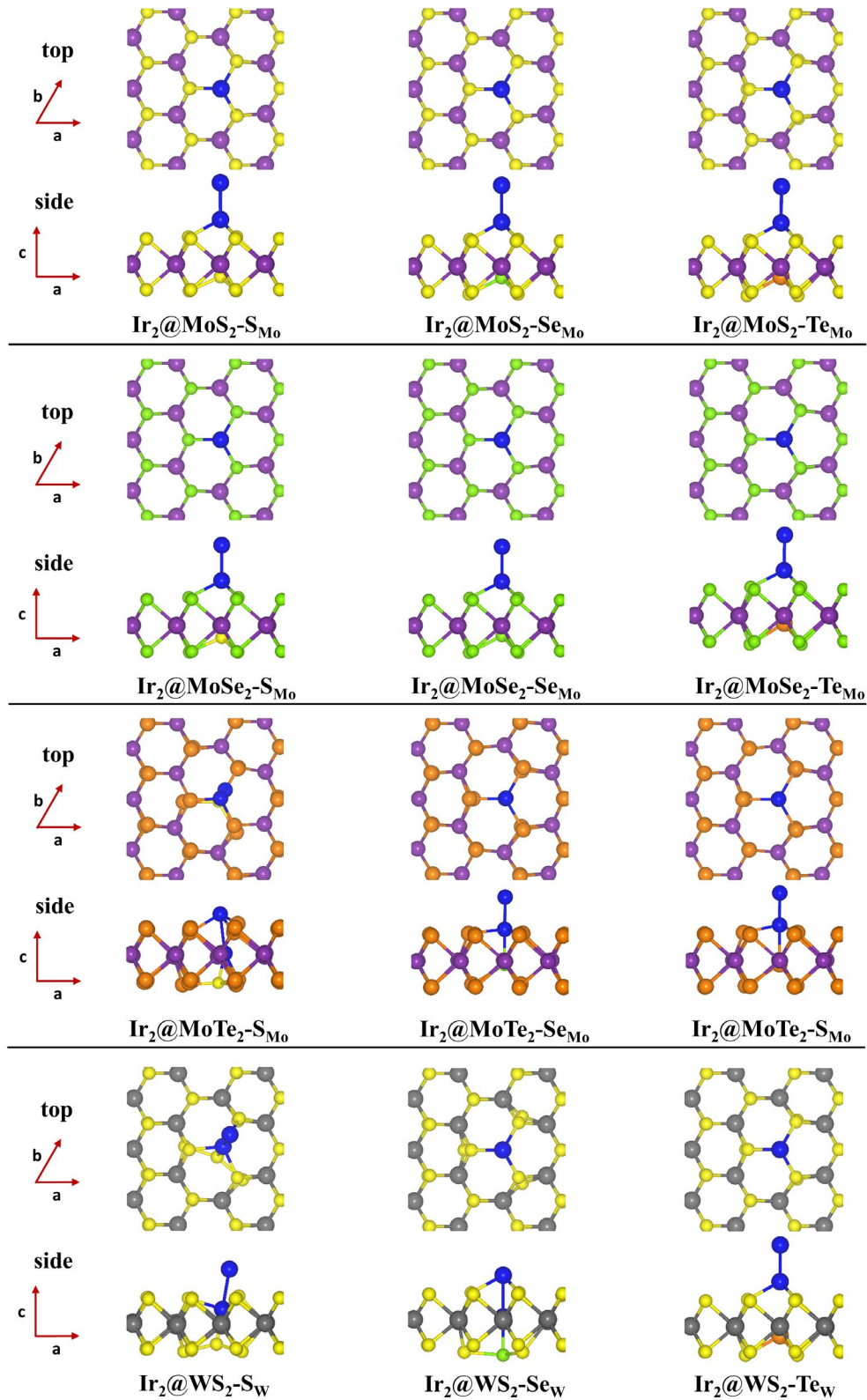
S5. Optimized structural parameters of Ir₂@TMD-X_M nanosheets.

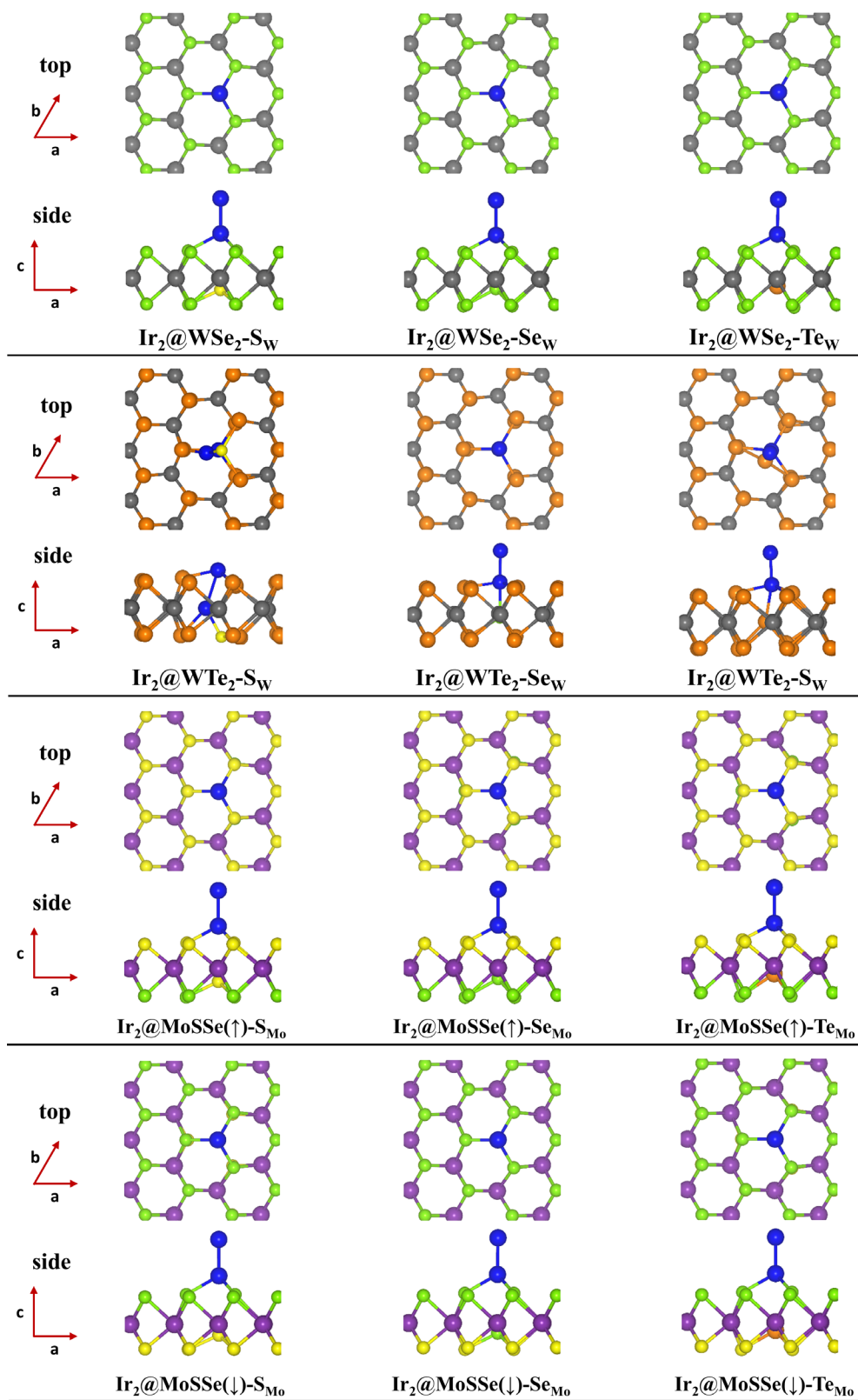
Table S3. Binding energies E_b (eV), included angles θ ($^\circ$), degrees of tilt ρ (%), distances d (\AA), Bader charges ΔQ (e) of 54 Ir₂@TMD-X_M structures.

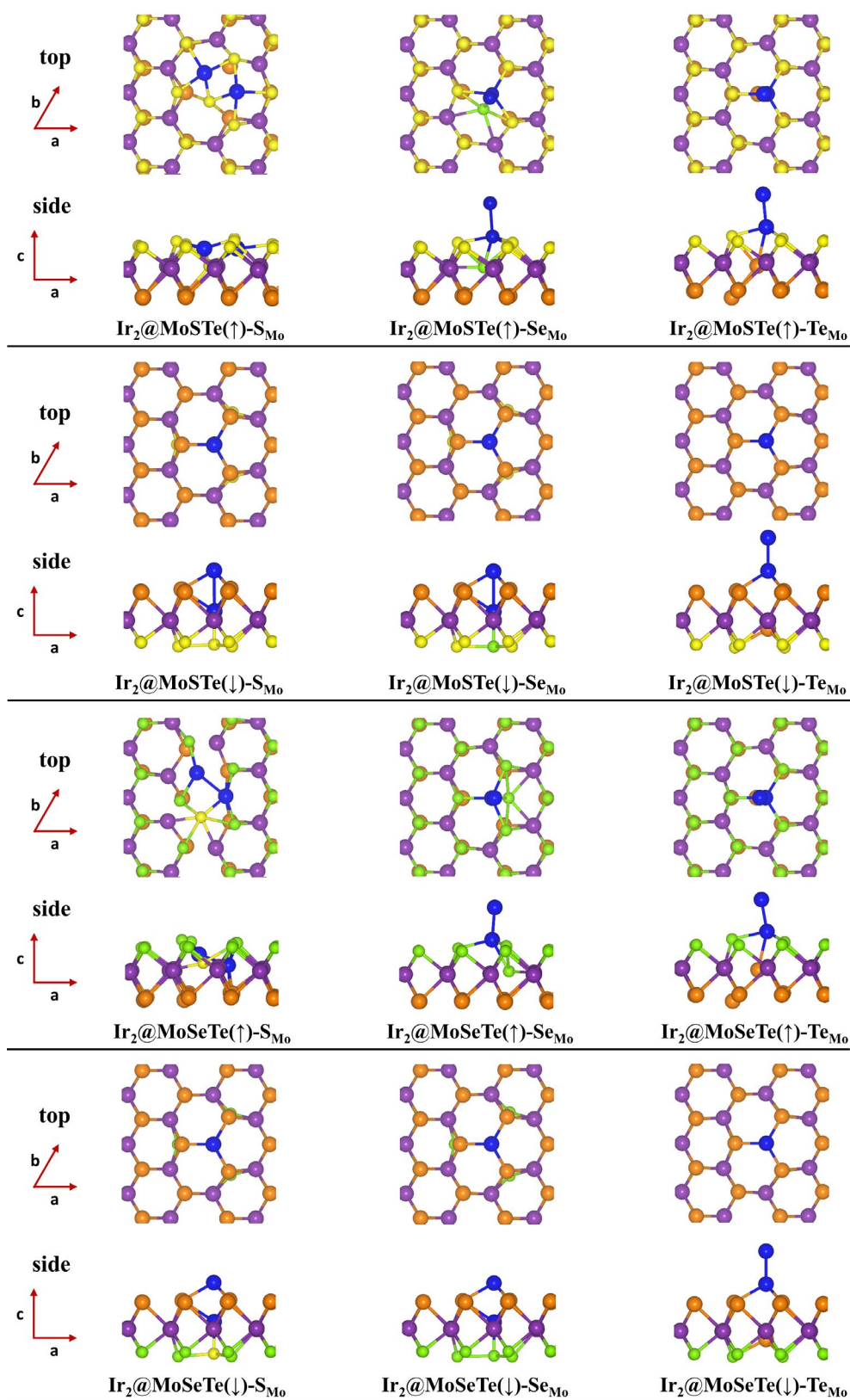
TMDs	Defect	E_b	θ	ρ	d_{Ir^A}	d_{Ir^B}	$d_{\text{Ir}^A-\text{Ir}^B}$	$d_{\text{Ir}^A-\text{def}}$	ΔQ	ΔQ_{Ir^A}	ΔQ_{Ir^B}
MoS ₂	S _{Mo}	-4.84	0.51	0.89	3.46	1.19	2.28	3.52	-0.221	0.144	-0.365
	Se _{Mo}	-4.25	0.51	0.89	3.47	1.19	2.28	3.46	-0.224	0.150	-0.373
	Te _{Mo}	-3.69	0.69	1.20	3.48	1.20	2.28	3.36	-0.228	0.154	-0.382
MoSe ₂	S _{Mo}	-4.22	0.34	0.59	3.49	1.21	2.28	3.67	0.050	0.168	-0.118
	Se _{Mo}	-3.80	0.48	0.84	3.50	1.22	2.28	3.57	0.048	0.184	-0.136
	Te _{Mo}	-3.41	1.04	1.82	3.51	1.24	2.28	3.41	0.053	0.193	-0.140
MoTe ₂	S _{Mo}	-7.11	13.73	24.42	1.01	-1.72	2.81	2.28	0.752	0.468	0.284
	Se _{Mo}	-4.10	1.35	2.35	2.73	0.47	2.27	2.52	0.621	0.327	0.294
	Te _{Mo}	-3.65	0.45	0.79	2.93	0.69	2.24	2.78	0.578	0.319	0.259
WS ₂	S _W	-4.92	18.74	33.92	1.89	-0.64	2.67	2.33	-0.162	0.055	-0.217
	Se _W	-5.91	0.14	0.24	1.17	-1.41	2.58	2.35	-0.040	-0.141	0.101
	Te _W	-3.30	0.28	0.49	3.46	1.19	2.27	3.34	-0.207	0.136	-0.342
WSe ₂	S _W	-4.02	0.48	0.85	3.51	1.23	2.28	3.66	0.067	0.156	-0.089
	Se _W	-3.57	0.16	0.28	3.51	1.23	2.28	3.55	0.064	0.215	-0.152
	Te _W	-3.19	1.99	3.47	3.60	1.33	2.27	3.37	0.068	0.142	-0.075
WTe ₂	S _W	-6.94	18.03	32.55	0.81	-1.86	2.80	2.27	0.794	0.502	0.292
	Se _W	-3.94	1.07	1.87	2.78	0.53	2.25	2.55	0.601	0.343	0.258
	Te _W	-3.92	5.37	9.40	3.13	0.87	2.27	2.74	0.594	0.259	0.335
MoSSe(\uparrow)	S _{Mo}	-3.86	0.50	0.87	3.39	1.14	2.25	3.51	-0.228	0.132	-0.350
	Se _{Mo}	-4.04	0.29	0.51	3.84	1.16	2.27	3.39	-0.228	0.113	-0.341
	Te _{Mo}	-3.54	0.06	0.11	3.46	1.19	2.27	3.24	-0.230	0.133	-0.363
MoSSe(\downarrow)	S _{Mo}	-3.96	0.23	0.40	3.62	1.33	2.29	3.74	0.076	0.142	-0.065
	Se _{Mo}	-4.17	0.91	1.59	3.37	1.33	2.29	3.68	0.076	0.145	-0.068
	Te _{Mo}	-3.79	0.32	0.56	3.62	1.33	2.29	3.58	0.076	0.135	-0.058
MoSTe(\uparrow)	S _{Mo}	-8.66	89.99	> 5e5	-0.07	-0.07	2.56	2.32	-0.189	-0.086	-0.102
	Se _{Mo}	-3.62	7.67	13.48	3.06	0.78	2.29	2.42	-0.251	0.060	-0.310
	Te _{Mo}	-2.99	5.47	9.58	3.20	0.97	2.24	2.73	-0.196	0.123	-0.319
MoSTe(\downarrow)	S _{Mo}	-6.00	0.54	0.95	1.45	-1.28	2.73	2.23	0.753	0.465	0.289
	Se _{Mo}	-6.07	0.30	0.52	1.41	-1.33	2.74	2.35	0.901	0.491	0.410

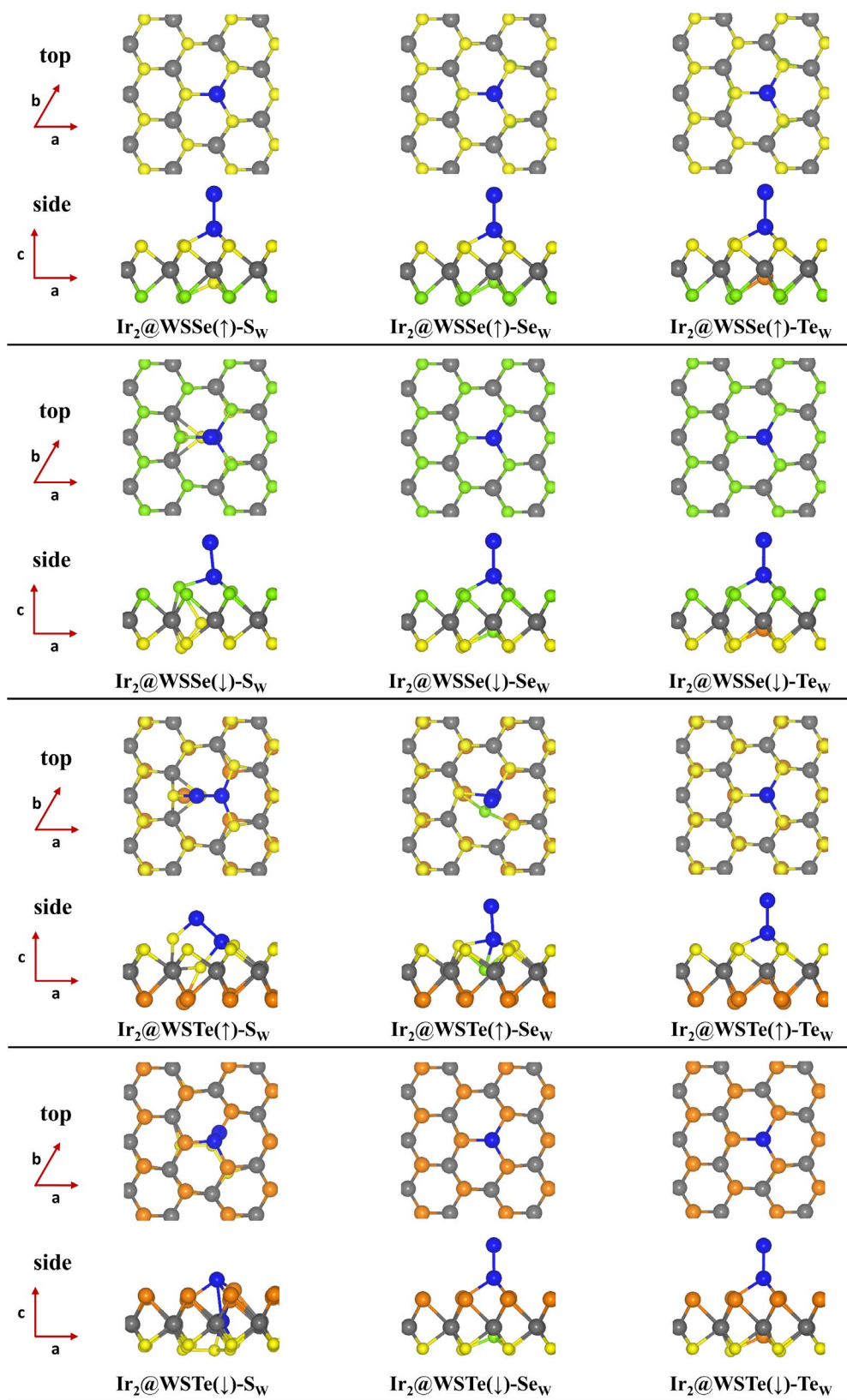
	Te _{Mo}	-3.90	0.07	0.12	3.75	1.49	2.26	3.39	0.472	0.165	0.306
MoSeTe(↑)	S _{Mo}	-8.95	73.85	345.28	1.26	-0.30	2.51	2.26	0.403	0.208	0.195
	Se _{Mo}	-3.78	4.56	7.97	3.03	0.79	2.25	2.48	0.050	0.156	-0.105
	Te _{Mo}	-3.27	9.80	17.27	3.18	0.95	2.26	2.75	0.146	0.205	-0.059
MoSeTe(↓)	S _{Mo}	-6.23	0.61	1.06	1.37	-1.35	2.72	2.23	0.754	0.472	0.281
	Se _{Mo}	-6.21	0.39	0.68	1.32	-1.41	2.73	2.37	0.799	0.454	0.345
	Te _{Mo}	-3.87	0.07	0.12	3.77	1.46	2.31	3.96	0.467	0.210	0.257
WSSe(↑)	S _w	-4.20	0.33	0.58	3.38	1.13	2.25	3.50	-0.207	0.213	-0.420
	Se _w	-3.67	0.11	0.20	3.40	1.15	2.25	3.39	-0.209	0.138	-0.348
	Te _w	-3.10	0.48	0.83	3.42	1.17	2.26	3.23	-0.207	0.187	-0.394
WSSe(↓)	S _w	-4.19	5.91	10.36	3.41	1.15	2.27	3.16	0.125	0.208	-0.083
	Se _w	-3.75	0.34	0.59	3.59	1.30	2.29	3.64	0.079	0.179	-0.100
	Te _w	-3.35	0.52	0.91	3.58	1.29	2.28	3.51	0.081	0.161	-0.080
WSTe(↑)	S _w	-5.77	47.38	108.67	2.14	0.56	2.34	2.27	-0.316	-0.036	-0.281
	Se _w	-4.02	8.25	14.51	3.02	0.75	2.29	2.40	-0.210	0.094	-0.305
	Te _w	-2.71	0.31	0.55	3.36	1.14	2.23	2.97	-0.188	0.141	-0.330
WSTe(↓)	S _w	-6.99	13.22	23.50	1.09	-1.77	2.94	2.25	0.723	0.528	0.195
	Se _w	-3.80	0.72	1.25	3.74	1.47	2.26	4.06	0.493	0.194	0.299
	Te _w	-3.74	0.27	0.46	3.73	1.47	2.26	3.96	0.484	0.182	0.303
WSeTe(↑)	S _w	-6.12	51.63	126.29	1.28	-0.28	2.51	2.26	0.160	0.028	0.132
	Se _w	-3.48	0.09	0.15	2.93	1.15	2.22	2.74	0.082	0.161	-0.079
	Te _w	-3.25	9.66	17.02	3.14	1.17	2.26	2.73	0.156	0.201	-0.046
WSeTe(↓)	S _w	-4.33	9.02	15.87	3.43	1.17	2.29	3.30	0.575	0.250	0.324
	Se _w	-3.97	0.02	0.04	3.65	1.30	2.25	3.97	0.474	0.198	0.276
	Te _w	-3.74	0.15	0.26	3.65	1.29	2.28	3.78	0.482	0.224	0.258

S6. Optimized configurations of $\text{Ir}_2@\text{TMD-X}_M$ nanosheets.









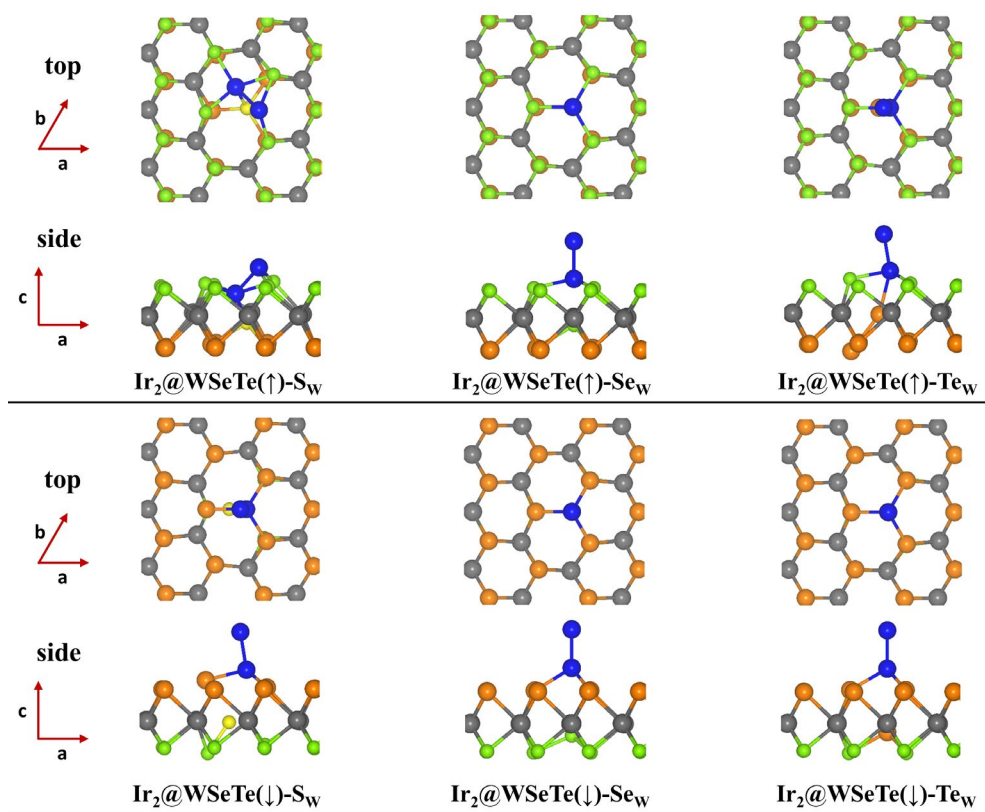


Fig. S3 Top and side views of $\text{Ir}_2@TMD\text{-}X_M$ ($M = \text{Mo}, \text{W}$; $X = \text{S}, \text{Se}, \text{Te}$) nanosheets. The yellow, green, orange, purple, grey and blue balls represent S, Se, Te, Mo, W and Ir atoms, respectively.

S7. The dissociation energy of top Ir atom and Ir₂ from Ir₂@TMD-X_M configurations.

In order to further verify the stability of the composite structures, the dissociation energies $E_d(\text{Ir}_2)$ and $E_d(\text{Ir}^A)$ are plotted in Figure S3, using the following formula:

$$E_d = E_{\text{Ir}^A/\text{Ir}_2} + E_{\text{re}} - E_{\text{Ir}_2@\text{TMD-X}_M}$$

where $E_{\text{Ir}_2@\text{TMD-X}_M}$, $E_{\text{Ir}^A/\text{Ir}_2}$ and E_{re} are the energies of the adsorbed Ir₂ dimer TMD systems, freestanding Ir^A atom or Ir₂ dimer, the remain part after dissociating, respectively.

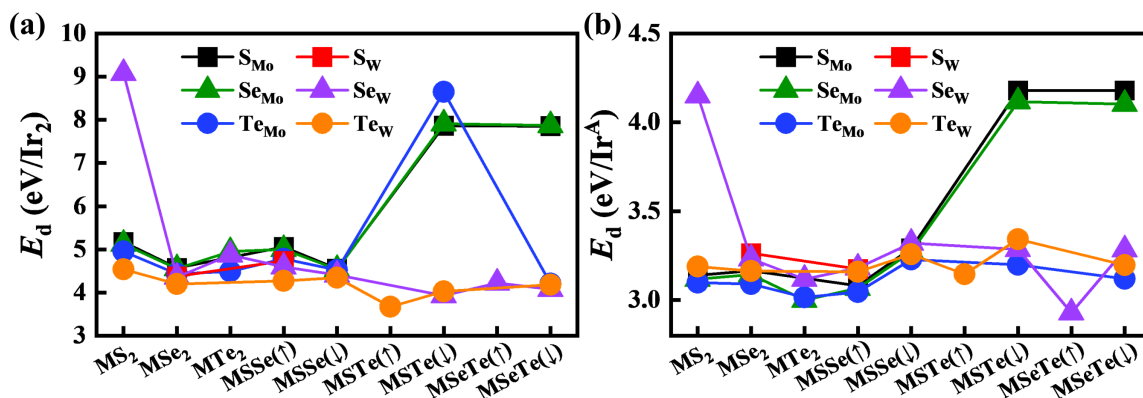


Fig. S4 The dissociation energy E_d for (c) Ir₂ dimer and (d) top Ir^A atom dissociating from composite systems. Here M (= Mo, W) in the abscissa is the same as M of X_M in legend.

S8. Magnetic parameters of vertical Ir₂@TMD-X_M nanosheets.

Table S4. MAEs (meV), total magnetic moments M (μ_B), spin moments M_S (μ_B) and orbital moments M_L (μ_B) of 37 vertical Ir₂@TMD-X_M structures.

TMDs	Defect	MAE	M_{tot}	$M(\text{Ir}_2)$	Ir ^A				Ir ^B			
					M_S^{\parallel}	M_S^{\perp}	M_L^{\parallel}	M_L^{\perp}	M_S^{\parallel}	M_S^{\perp}	M_L^{\parallel}	M_L^{\perp}
MoS ₂	S _{Mo}	71.09	1.644	1.603	0.953	0.039	0.336	1.400	0.209	0.268	0.073	0.017
	Se _{Mo}	70.33	1.672	1.639	0.903	0.060	0.347	1.388	0.211	0.273	0.077	0.017
	Te _{Mo}	70.83	1.695	1.673	0.920	0.082	0.343	1.375	0.219	0.278	0.074	0.018
MoSe ₂	S _{Mo}	70.71	1.741	1.724	0.918	0.097	0.348	1.354	0.235	0.295	0.097	0.035
	Se _{Mo}	69.33	1.762	1.761	0.932	0.120	0.351	1.344	0.241	0.303	0.097	0.035
	Te _{Mo}	70.71	1.764	1.783	0.950	0.139	0.342	1.335	0.243	0.307	0.099	0.034
MoTe ₂	Se _{Mo}	-3.64	0.078	0.173	0.229	-0.083	0.019	0.297	-0.026	0.006	-0.001	-0.047
	Te _{Mo}	-1.90	-0.033	-0.102	-0.150	-0.086	0.020	0.153	0.035	0.020	0.026	0.027
WS ₂	Se _W	0	0	0	0	0	0	0	0	0	0	0
	Te _W	75.93	1.698	1.577	0.903	0.021	0.313	1.415	0.215	0.280	0.088	0.025
WSe ₂	S _W	70.69	1.702	1.705	0.924	0.072	0.323	1.366	0.235	0.301	0.112	0.045
	Se _W	70.63	1.732	1.749	0.941	0.100	0.326	1.353	0.243	0.309	0.110	0.044
	Te _W	72.61	1.735	1.768	0.958	0.118	0.316	1.346	0.244	0.308	0.109	0.044
WTe ₂	Se _W	0.85	-0.025	-0.046	-0.074	-0.004	0.003	-0.037	0.008	-0.002	-0.005	0.010
MoSSc(↑)	S _{Mo}	79.13	1.388	1.371	0.836	-0.070	0.296	1.467	0.196	0.260	0.076	0.016
	Se _{Mo}	74.46	1.553	1.534	0.877	0.010	0.331	1.424	0.199	0.270	0.082	0.014
	Te _{Mo}	73.67	1.636	1.622	0.914	0.060	0.325	1.387	0.213	0.279	0.078	0.015
MoSSc(↓)	S _{Mo}	65.22	1.815	1.783	0.923	0.137	0.378	1.324	0.237	0.277	0.080	0.043
	Se _{Mo}	65.23	1.820	1.800	0.923	0.151	0.389	1.320	0.237	0.281	0.084	0.043
	Te _{Mo}	67.75	1.785	1.779	0.929	0.139	0.378	1.335	0.233	0.279	0.085	0.041
MoSTe(↓)	S _{Mo}	0	0	0	0	0	0	0	0	0	0	0
	Se _{Mo}	0	0	0	0	0	0	0	0	0	0	0
	Te _{Mo}	64.73	1.808	1.842	0.889	0.155	0.465	1.402	0.141	0.135	0.091	-0.004
MoSeTe(↓)	S _{Mo}	0	0	0	0	0	0	0	0	0	0	0
	Se _{Mo}	0	0	0	0	0	0	0	0	0	0	0
	Te _{Mo}	65.88	1.811	1.851	0.947	0.165	0.389	1.330	0.249	0.297	0.103	0.054
WSSc(↑)	S _W	82.01	1.254	1.273	0.823	-0.108	0.286	1.492	0.201	0.273	0.098	0.016
	Se _W	81.35	1.317	1.343	0.838	-0.079	0.279	1.476	0.202	0.275	0.087	0.017
	Te _W	82.14	1.389	1.432	0.872	-0.036	0.280	1.448	0.202	0.276	0.092	0.020
WSSc(↓)	Se _W	67.66	1.801	1.801	0.945	0.133	0.350	1.328	0.246	0.298	0.099	0.047

	Te _w	69.19	1.779	1.796	0.949	0.134	0.346	1.335	0.241	0.298	0.104	0.047
WSTe(↑)	Te _w	79.06	0.917	1.029	0.909	0.083	0.358	1.354	0.239	0.276	0.103	0.067
WSTe(↓)	Se _w	69.68	1.721	1.742	0.717	-0.159	0.186	1.430	0.134	0.258	0.110	-0.012
	Te _w	73.52	1.679	1.724	0.914	0.072	0.356	1.376	0.236	0.275	0.104	0.067
WSeTe(↑)	Se _w	-0.98	-0.043	-0.077	-0.131	0.010	-0.023	0.038	0.023	0.041	0.019	0.027
WSeTe(↓)	Se _w	71.09	1.688	1.709	0.918	0.056	0.321	1.367	0.241	0.284	0.114	0.072
	Te _w	68.72	1.780	1.829	0.959	0.139	0.354	1.343	0.239	0.293	0.118	0.062

S9. Projected density of states of $\text{Ir}_2@TMD-X_M$ nanosheets.

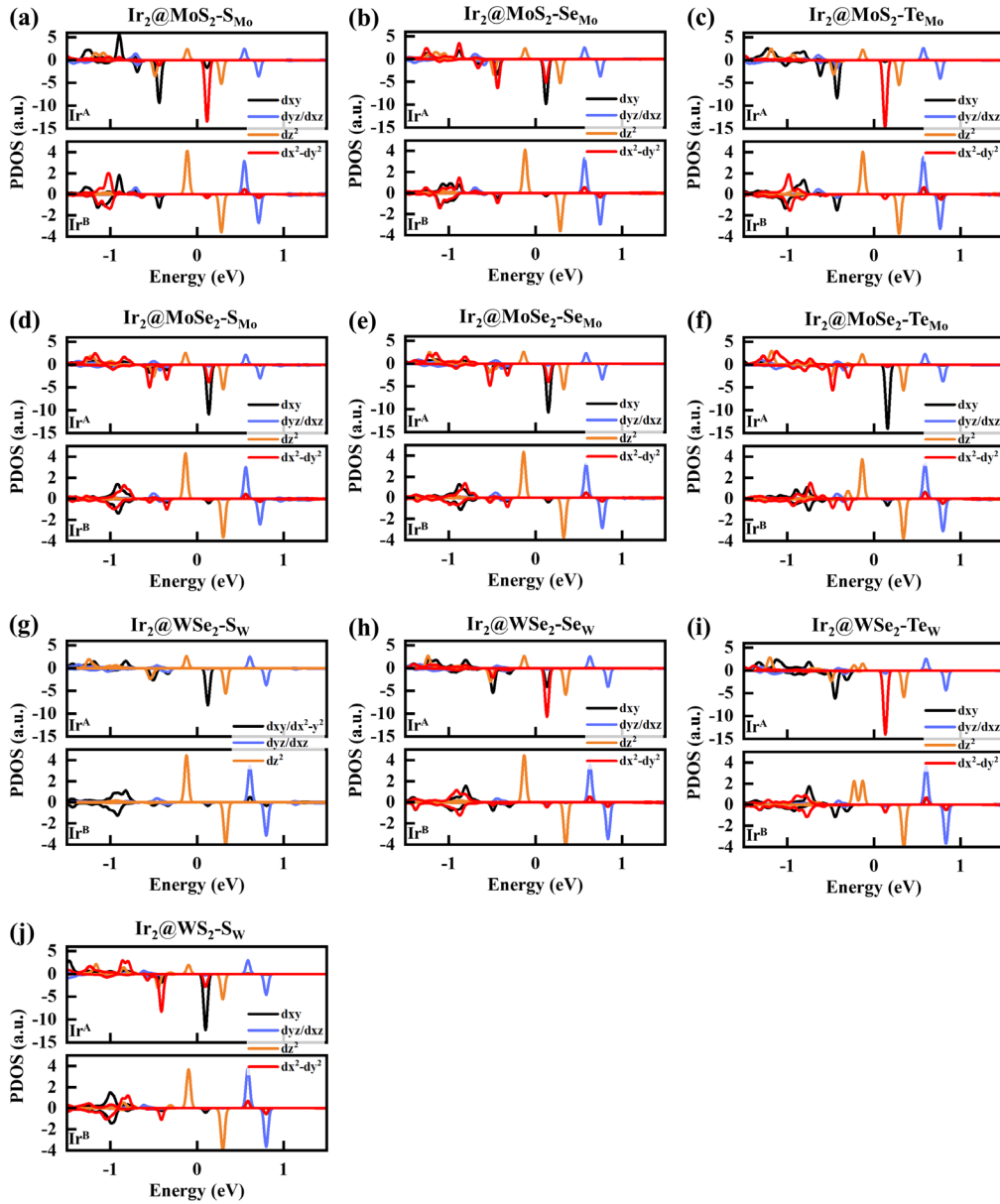


Fig. S5 Projected density of states of d orbitals of Ir^A and Ir^B atoms in $\text{Ir}_2@MX_2-X_M$ ($M = \text{Mo}, \text{W}; X = \text{S}, \text{Se}, \text{Te}$) structures.

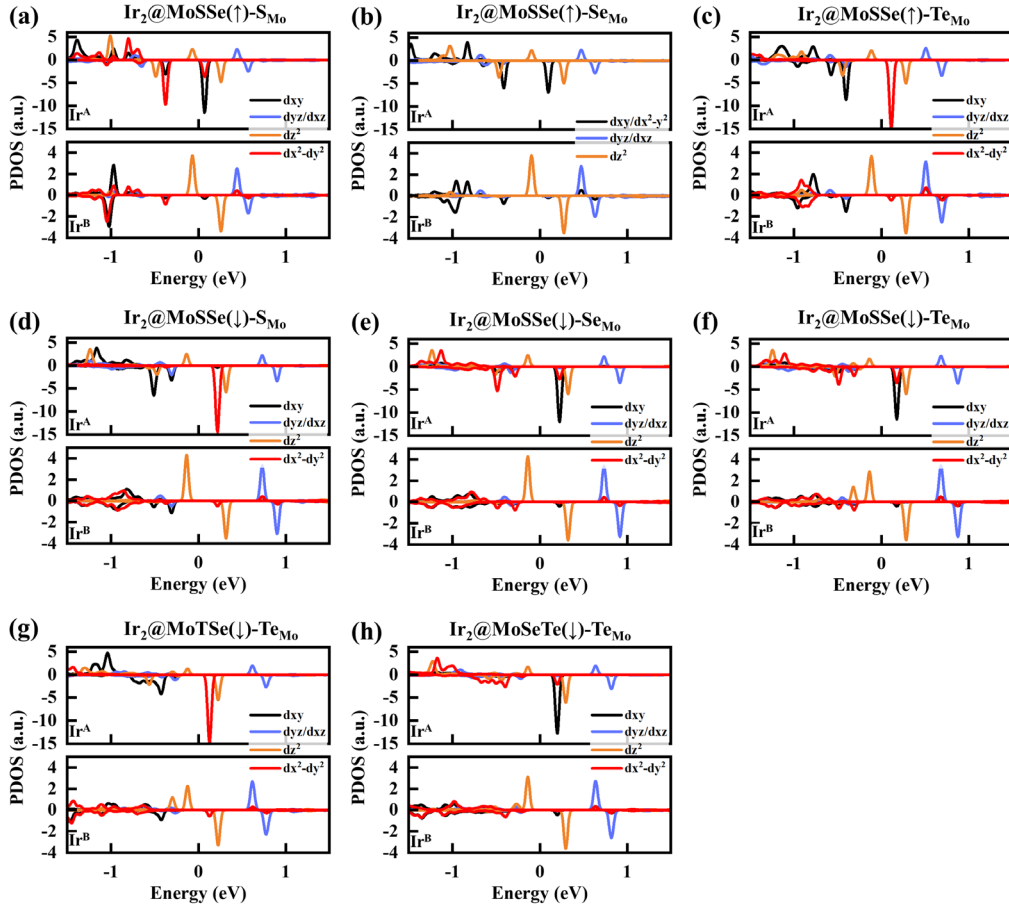


Fig. S6 Projected density of states of d orbitals of Ir^A and Ir^B atoms in Ir₂@MoXY-X_{Mo} (X, Y = S, Se, Te; X≠Y) structures.

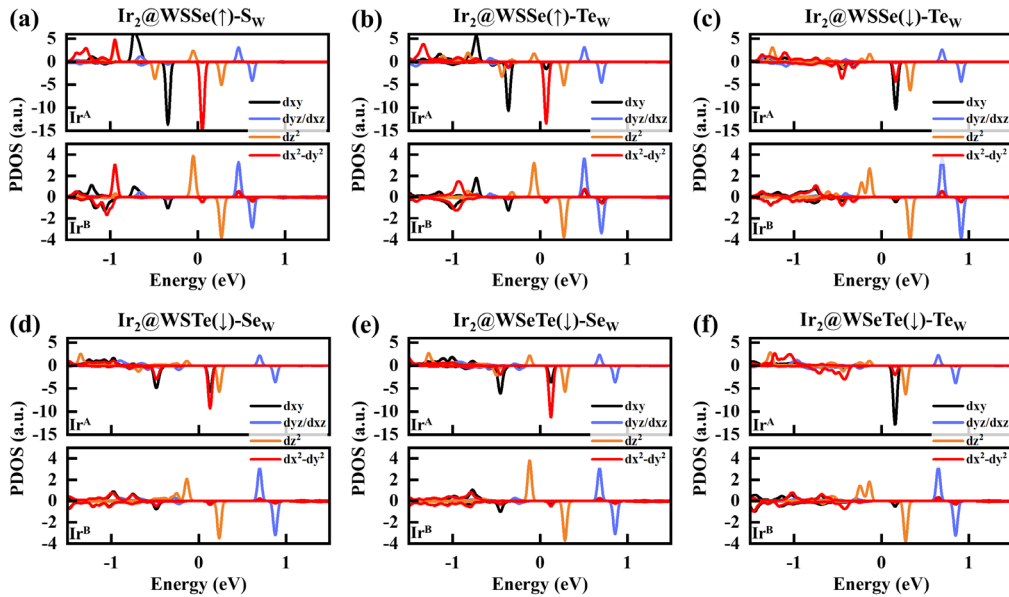
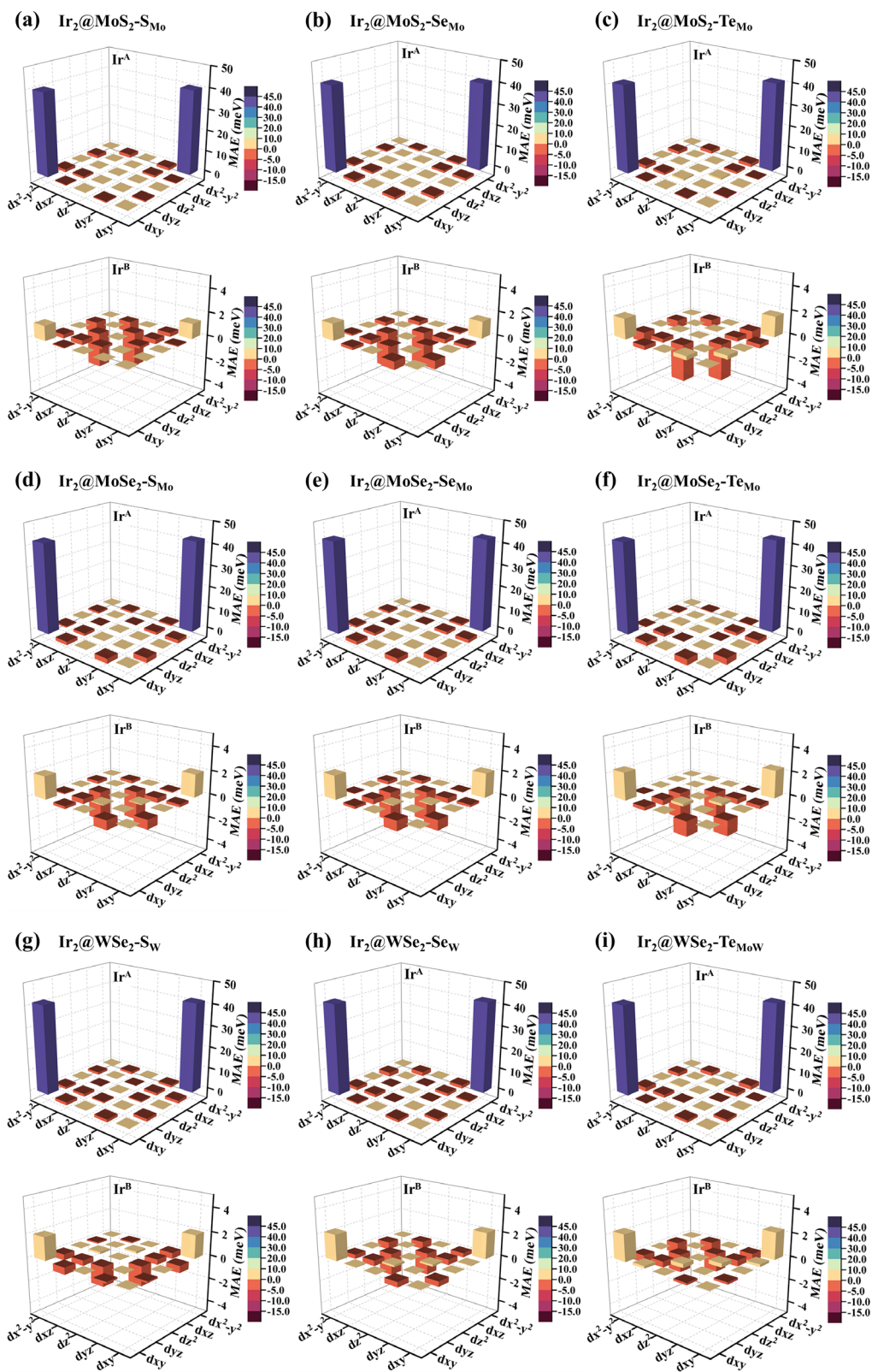


Fig. S7 Projected density of states of d orbitals of Ir^A and Ir^B atoms in Ir₂@WXY-X_W (X, Y = S, Se, Te; X≠Y) structures.

S10. The d-orbital resolved MAE of Ir atoms in $\text{Ir}_2@\text{TMD-X}_M$ nanosheets.



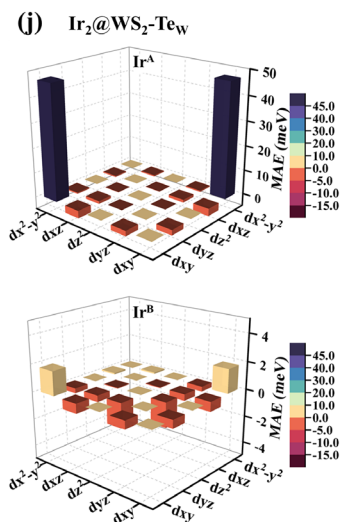
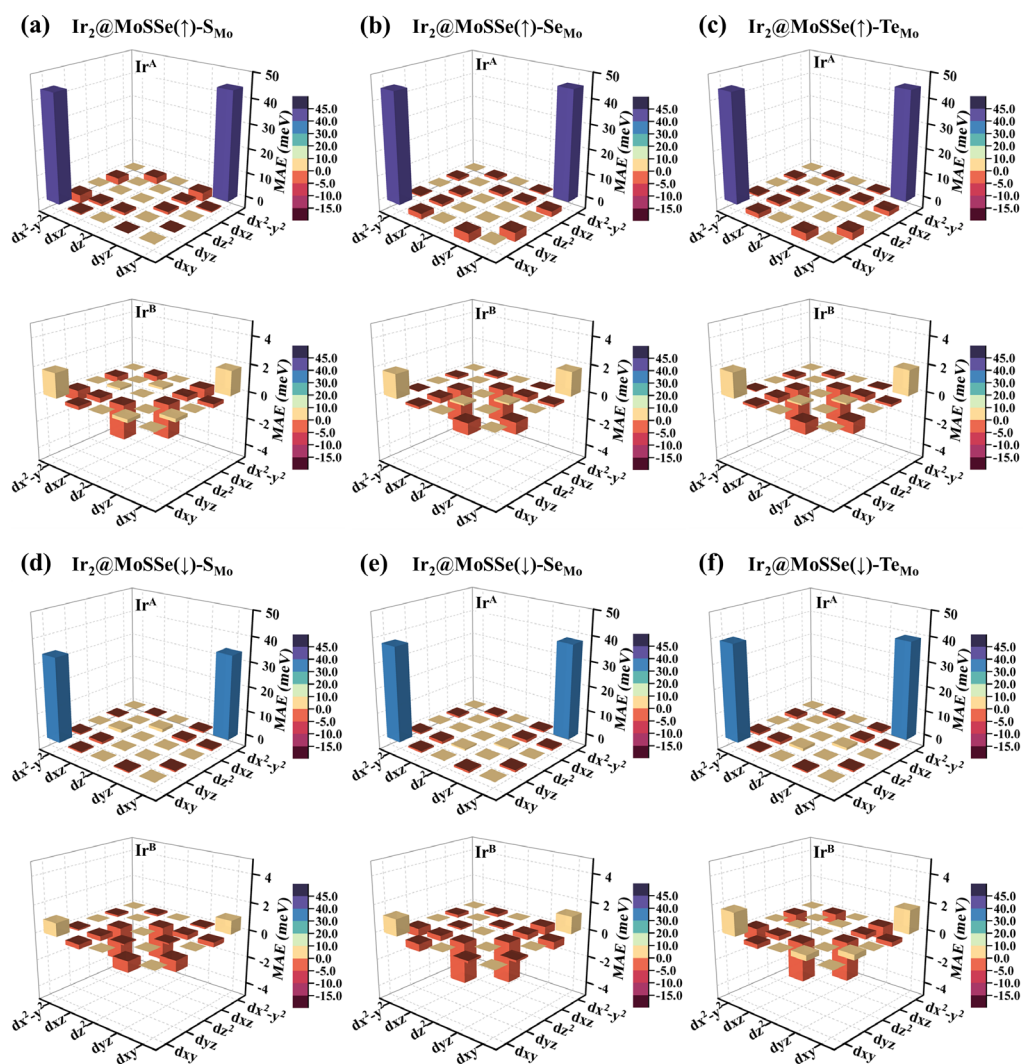


Fig. S8 The d-orbital resolved MAE of Ir^A and Ir^B atoms in Ir₂@MX₂-X_M (M = Mo, W; X = S, Se, Te) structures.



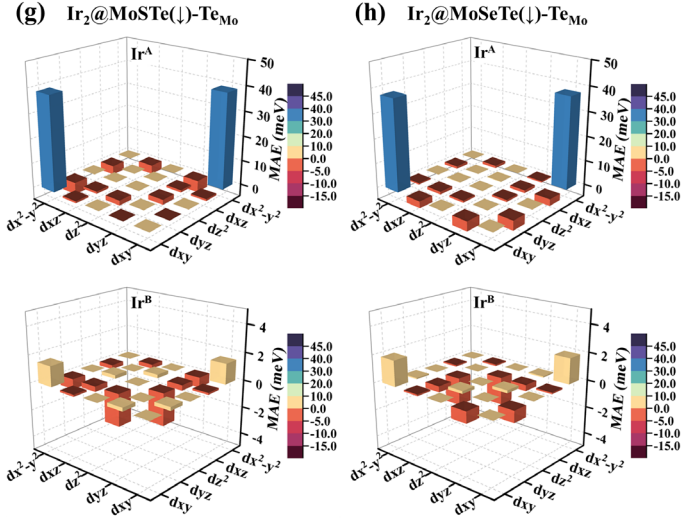
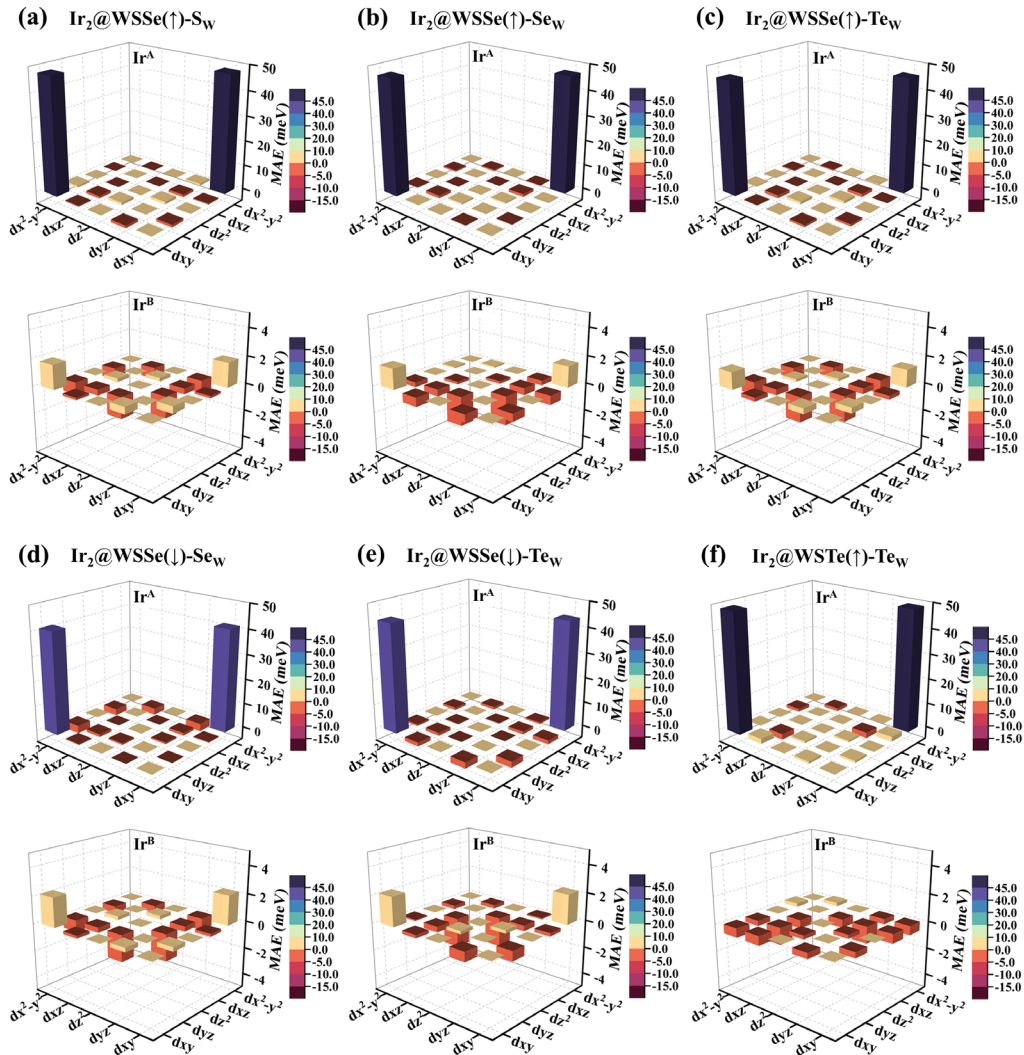


Fig. S9 The d-orbital resolved MAE of Ir^A and Ir^B atoms in Ir₂@MoXY-X_{M0} (X, Y = S, Se, Te; X≠Y) structures.



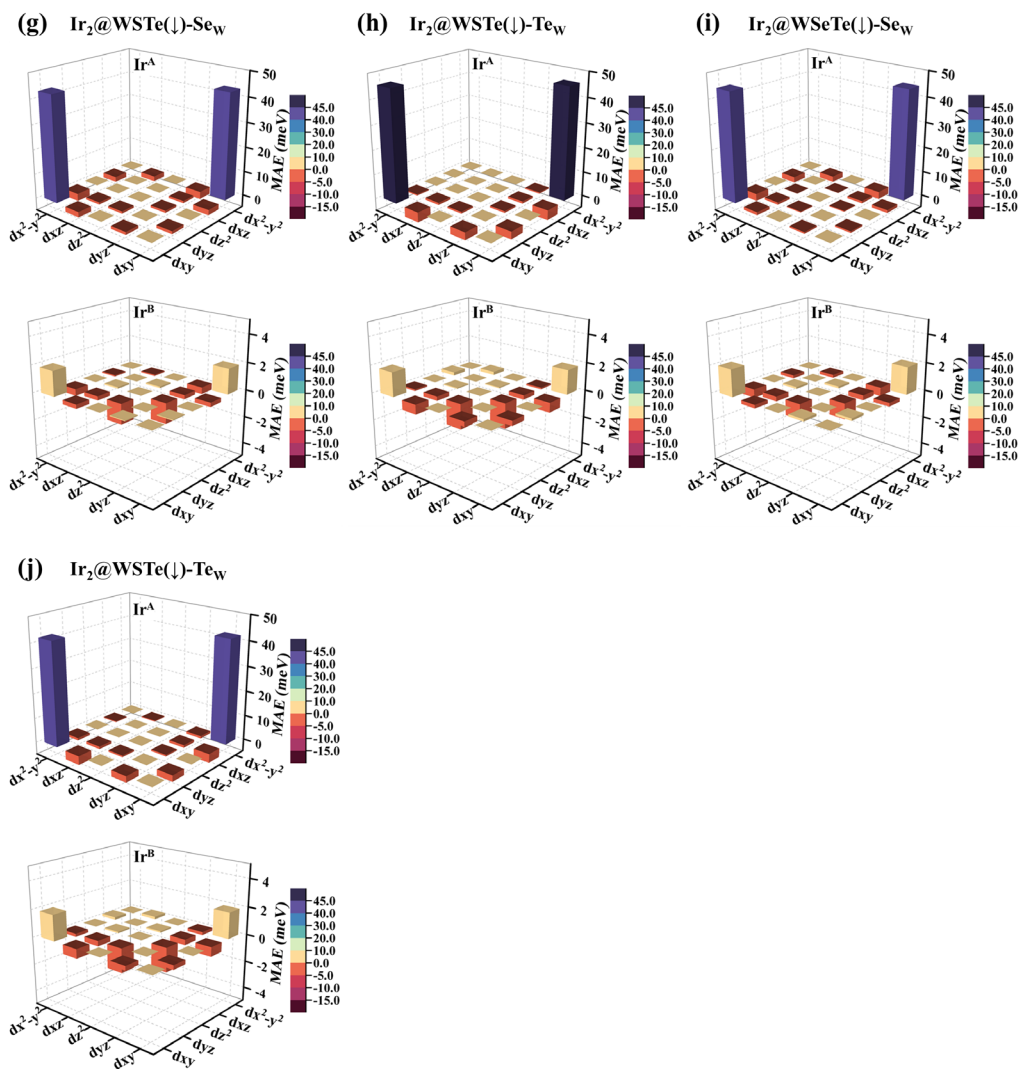


Fig. S10 The d-orbital resolved MAE of Ir^A and Ir^B atoms in Ir₂@WXY-X_w (X, Y = S, Se, Te; X≠Y) structures.

S11. The relationship among ΔV , ϵ_{dd} , ϵ_{ud} of vertical Ir_2 above TMD-X_M nanosheets.

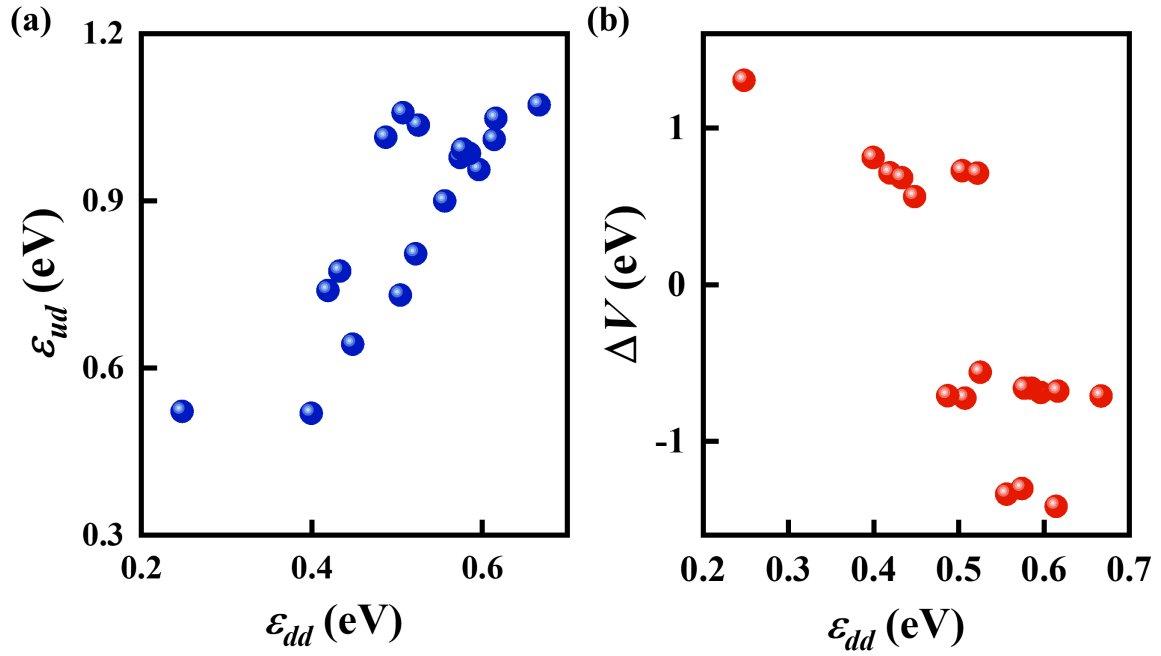


Fig. S11 (a) The energy eigenvalues difference between occupied and unoccupied states in cross-spin states ϵ_{ud} as a function of the one in minority states ϵ_{dd} . (b) The average electrostatic potential differences ΔV (eV) as a function of energy eigenvalues difference between occupied and unoccupied states ϵ_{dd} in minority spin states.

S12. The values of ϵ_{dd} and ϵ_{ud} of vertical Ir_2 above Janus TMD- X_M nanosheets.

Table S5. Energy differences ϵ_{dd} and ϵ_{ud} of $\text{Ir}_2@$ Janus TMD- X_M monolayers with large MAEs (> 60 meV/ Ir_2).

Substrates	ϵ_{dd} (eV)			ϵ_{ud} (eV)		
	S_M	Se_M	Te_M	S_M	Se_M	Te_M
MoSSe(\uparrow)	0.448	0.504	0.522	0.643	0.731	0.805
MoSSe(\downarrow)	0.525	0.507	0.487	1.036	1.058	1.014
MoSTe(\uparrow)	-	-	-	-	-	-
MoSTe(\downarrow)	-	-	0.556	-	-	0.900
MoSeTe(\uparrow)	-	-	-	-	-	-
MoSeTe(\downarrow)	-	-	0.596	-	-	0.956
WSSe(\uparrow)	0.399	0.419	0.433	0.519	0.739	0.774
WSSe(\downarrow)	-	0.667	0.616	-	1.072	1.048
WSTe(\uparrow)	-	-	0.248	-	-	0.522
WSTe(\downarrow)	-	0.614	0.574	-	1.010	0.978
WSeTe(\uparrow)	-	-	-	-	-	-
WSeTe(\downarrow)	-	0.585	0.577	-	0.985	0.993